AMENDMENTS TO THE SPECIFICATION

Please replace the two paragraphs beginning at page 5, line 1, with the following amended paragraphs:

Referring now to **Fig. 1**, wherein a first wafer 100 is illustrated as having copper structures 110 embedded therein, and rise above the interlayer dielectric layer 102 with a substantially uniform height. Illustrated also are copper structures 106, 108 embedded, and rise above the interlayer dielectric layer 104 of a second wafer 101 with a substantially uniform height. In one embodiment, the uniformity of heights of any or all the copper structures 106, 108, 110 and 112 on the wafers 100 and 101 can be expressed as a difference of no more than 5 nm between the height of one copper structure to another copper structure. In another embodiment, the height of the ~~cooper~~ copper structures 106, 108, 110 above the plane of the interlayer dielectric layers 102, 104 can be in a range of 100 - 300 nm.

With regard to Figure 1, the copper structures 108 are then aligned and bonded to the copper structures 110 so that they make interconnections between the wafers 100 and 101. The copper structure 106 is part of a ~~cooper~~ copper interconnect on the wafer 101 that does not need or require any connection to circuits that maybe interconnected by copper structures 110 on wafer 100.